

Amended Claims

1. (currently amended) An integrated photonic device comprising:
  - a substrate;
  - a photonic circuit etched onto said substrate;
  - a cladding layer positioned on said substrate, said cladding layer having a refractive index different from said circuit; and
  - an angled implantation disposed in said cladding layer, said ~~angle~~angled implantation optically connecting said photonic circuit with an outer surface of said cladding layer, wherein said angled implantation forms an angle of about 50 degrees or less with said substrate.
2. (original) The integrated photonic device according to claim 1, wherein said substrate comprises an oxide.
3. (original) The integrated photonic device according to claim 1, wherein said cladding layer comprises an oxide.
4. (original) The integrated photonic device according to claim 1, wherein said photonic circuit comprises a waveguide.
5. (original) The integrated photonic device according to claim 4, wherein said waveguide comprises SiON.

6. (original) The integrated photonic device according to claim 1, wherein said angled implantation forms an angle of about 50 degrees with said substrate.

7. (original) The integrated photonic device according to claim 1, wherein said angled implantation forms an angle less than 50 degrees with said substrate.

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8. (original) The integrated photonic device according to claim 1, wherein said angled implantation is injected with nitrogen and annealed to form a channel of SiON connecting said photonic circuit with an outer surface of said cladding layer.

9. (original) The integrated photonic device according to claim 1, wherein said photonic circuit has a refractive index of about 1.6 and said substrate has a refractive index of about 1.44.

10. (cancelled)

11. (cancelled)

12. (cancelled)

13. (cancelled)

14. (cancelled)

15. (currently amended) An integrated photonic circuit comprising:
- a substrate;
  - a photonic waveguide etched onto said substrate;
  - a cladding layer vertically disposed on said waveguide and substrate, said cladding layer having a refractive index different from said waveguide; and
- means to optically connect said photonic waveguide with an outer surface of said cladding layer, wherein said means to connect said photonic waveguide with said outer surface forms an angle of about 50 degrees or less with said substrate.
16. (original) The integrated photonic circuit according to claim 15, wherein said means to connect said photonic waveguide with said outer surface forms an angle of about 50 degrees with said substrate.
17. (original) The integrated photonic circuit according to claim 15, wherein said means to connect said photonic waveguide with said outer surface forms an angle of less than 50 degrees with said substrate.
18. (original) The integrated photonic circuit according to claim 15, wherein said waveguide comprises SiON.

19. (original) The integrated photonic circuit according to claim 15, wherein said waveguide has a refractive index of about 1.6 and said substrate has a refractive index of about 1.4.

20. (original) The integrated photonic circuit according to claim 15, wherein said substrate and said cladding comprise oxide.